



PATENT
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Ulrike Gruening et al.

Serial No.: 09/669,585

Filing Date: September 26, 2000

Entitled: IMPROVED TRENCH CAPACITOR
MEMORY CELL

Docket No.: 00P7925US (IFX-060PUS)

Group Art Unit: 2811

Examiner: C. Nguyen

#6/a

10/23/02

Smith

Certificate of Mailing (37 C.F.R. 1.8(a))

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10-10-02

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and Mail Deposit

By: Tanya Blount
Tanya Blount

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

In response to the Office Action date mailed May 17, 2002, please amend the above-identified application as follows:

In the Claims:

A clean copy of the amended claims is below, a comparison copy is attached:

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(Amended) A memory cell comprising:
a trench capacitor formed in a substrate;
a shallow transistor trench (STT) formed in the substrate;
a transistor comprising:
a first diffusion region, the first diffusion region couples the capacitor to
a gate of the transistor;

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